



Dr. Andrés Redondo-Cubero got his Ph.D. in Physics at the Autonomous University of Madrid (Spain) in 2010, where he continues as “Ramón y Cajal” researcher and lecturer. His main research topic is the modification and analysis of semiconductor materials for electronics by means of ion beam techniques. He has a large experience in the characterization of defects by ion channeling, in combination with X-ray diffraction. His scientific career includes formation in different international ion beam centers such as CMAM (Madrid), CTN (Lisbon), HZDR (Dresden), IFK (Jena), or ISOLDE (Geneva). He has about 60 publications in international scientific journals and circa 100 participation in conferences.